



P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	R _{DS(ON)} max	I _D max T _C = +25°C
001/	$32m\Omega$ @ $V_{GS} = -4.5V$	-13A
-20V	53mΩ @ V _{GS} = -2.5V	-10A

Features and Benefits

- 0.6mm Profile Ideal for Low Profile Applications
- PCB Footprint of 4mm²
- Low Gate Threshold Voltage
- Low On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

https://www.diodes.com/quality/product-definitions/

Description and Applications

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management Application
- Power Management Functions
- DC-DC Converters

Mechanical Data

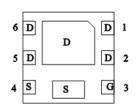
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208²
- Weight: 0.0065 grams (Approximate)

U-DFN2020-6 (Type F)

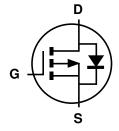




Top View Bottom View



Pin Out Bottom View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2040UFDF-7	U-DFN2020-6 (Type F)	3,000/Tape & Reel
DMP2040UFDF-13	U-DFN2020-6 (Type F)	10.000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/



Marking Information

Site 1



4D = Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020) M = Month (ex: 9 = September)

Date Code Key

Year	2016		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	D		Н		J	K	L	М	N	0	Р	R
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

Site 2



4D = Product Type Marking Code YWX = Date Code Marking Y = Year (ex: 0 = 2020) W = Week (ex: a = Week 27; z Represents Week 52 and 53) X = Internal Code (ex: U = Monday)

Date Code Key

Year	2016		2020	2021	2022	2023	2024	2025	2026	2027	2028	2029
Code	6		0	1	2	3	4	5	6	7	8	9
Week	1-26			27-52				53				
Code		Α	-Z		a-z				Z			
Internal Code	Sur	1	Mon		Tue	W	ed	Thu		Fri		Sat
Code	Т		U		V	V	٧	Х		Υ		Z



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Drain-Source Voltage	V _{DSS}	-20	V		
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) Vgs = -4.5V	lD	-6.1 -4.9	А		
Continuous Drain Current (Note 7) VGS = -4.5V	lo	-13 -10	А		
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	5)		I _{DM}	-35	Α
Continuous Source-Drain Diode Current (Note 6)	Is	-2.0	Α		
Avalanche Current (Note 8) L = 0.1mH	las	-17	Α		
Avalanche Energy (Note 8) L = 0.1mH			Eas	14	mJ

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	ReJA	149	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	ПӨЈА	95	C/VV
Total Power Dissipation (Note 6)	T _A = +25°C	PD	1.8	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	Reja	70	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	МӨЈА	45	G/VV
Thermal Resistance, Junction to Case (Note 7)	Steady State	$R_{ heta JC}$	16	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C	

Electrical Characteristics (T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)		·	•	•		
Drain-Source Breakdown Voltage	BVDSS	-20	_	_	V	V _G S = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-1	μΑ	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 12V$, $V_{DS} = 0V$
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-0.6	_	-1.5	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$
Static Drain-Source On-Resistance	Descent	_	22	32	mO	V _G S = -4.5V, I _D = -8.9A
Static Diain-Source On-Nesistance	RDS(ON)	_	31	53	11122	V _{GS} = -2.5V, I _D = -6.9A
Diode Forward Voltage	VsD	_	-0.7	-1.2	V	V _G S = 0V, I _S = -2.9A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	Ciss	_	834	_		101/1/
Output Capacitance	Coss	_	133	_	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	105	_		1 - 1.0WH12
Gate Resistance	Rg	_	4.9	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1.0MHz$
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	8.6	_		
Total Gate Charge (V _{GS} = -8V)	Qg	_	19	_	nC	Vps = -6V. lp = -8.9A
Gate-Source Charge	Qgs	_	1.5	_	110	VDS = -0V, ID = -0.9A
Gate-Drain Charge	Qgd	_	2.5	_		
Turn-On Delay Time	td(ON)	_	5.8	_		
Turn-On Rise Time	tr	_	7.7	_	ns	$V_{DD} = -6V$, $R_L = 6\Omega$
Turn-Off Delay Time	t _{D(OFF)}	_	28.1	_	115	V_{GS} = -4.5V, R_G = 6 Ω , I_D = -1A
Turn-Off Fall Time	tF	_	14.6			
Body Diode Reverse Recovery Time	trr	_	9.8	_	ns	IF = -8.9A, di/dt = -100A/µs
Body Diode Reverse Recovery Charge	Qrr	_	2.7	_	nC	IF = -8.9A, di/dt = -100A/µs

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad).
 I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.



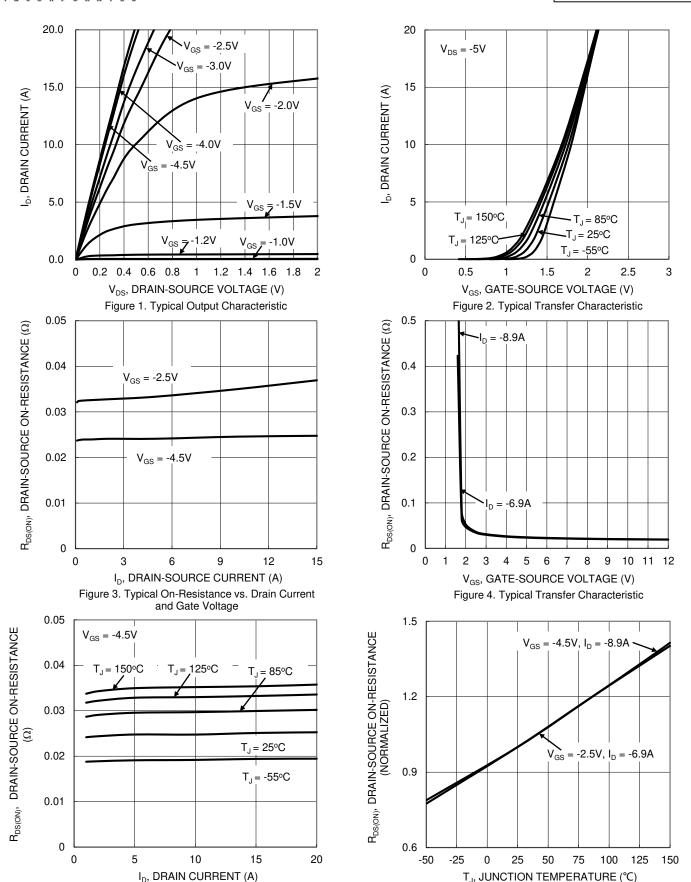


Figure 6. On-Resistance Variation with Temperature

Figure 5. Typical On-Resistance vs. Drain Current and

Temperature



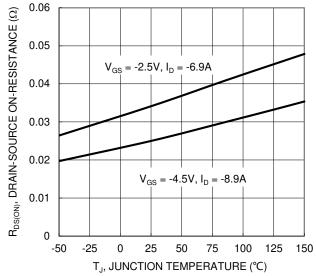


Figure 7. On-Resistance Variation with Temperature

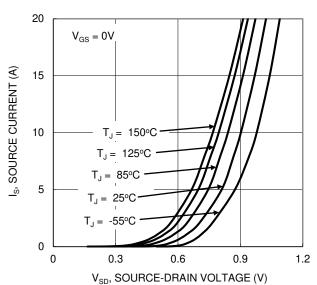


Figure 9. Diode Forward Voltage vs. Current

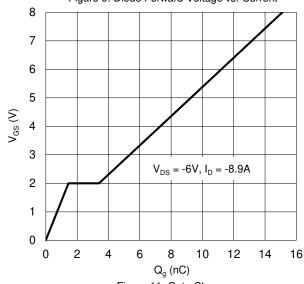


Figure 11. Gate Charge

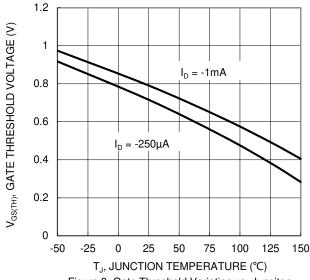


Figure 8. Gate Threshold Variation vs. Junciton Temperature

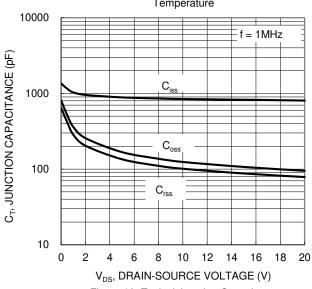


Figure 10. Typical Junction Capacitance

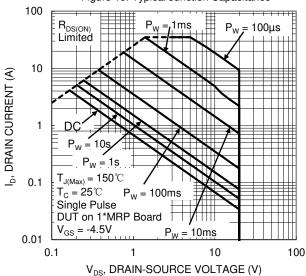


Figure 12. SOA, Safe Operation Area



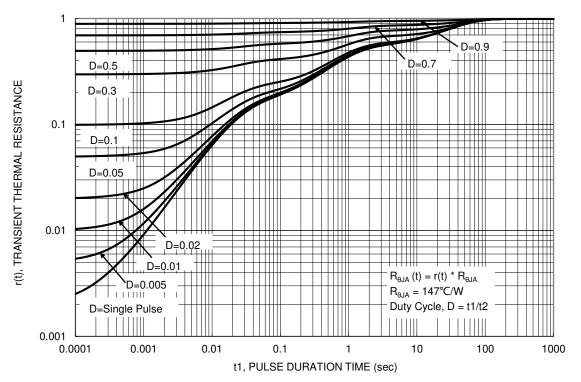


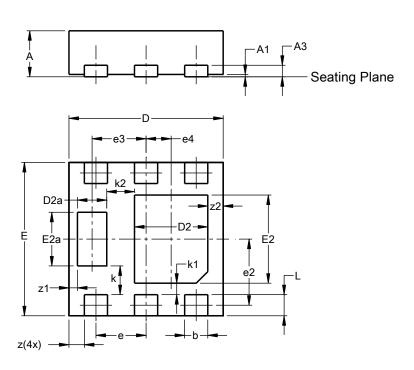
Figure 13. Transient Thermal Resistance



Package Outline Dimension

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)

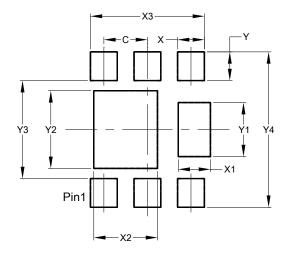


U-DFN2020-6								
	_ `	e F)						
Dim	Min	Max	Тур					
Α	0.57	0.63	0.60					
A 1	0.00	0.00 0.05 0.03						
А3	-	0.15						
b	0.25	0.35	0.30					
D	1.95	2.05	2.00					
D2	0.85	1.05	0.95					
D2a	0.33	0.33 0.43 0.3						
Е	1.95	2.05	2.00					
E2	1.05	1.25	1.15					
E2a	0.65	0.75	0.70					
е	(0.65 BS	С					
e2	C	.863 BS	SC					
е3		0.70 BS	С					
e4	C	.325 BS	SC					
k		0.37 BS						
k1	(0.15 BS	С					
k2		0.36 BS						
L	0.225	0.325	0.275					
Z		0.20 BS	С					
z1	C	.110 BS	SC					
z2	(0.20 BS	С					
All C	imens	ions in	mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

U-DFN2020-6 (Type F)



Dimensions	Value (in mm)
С	0.650
Х	0.400
X1	0.480
X2	0.950
Х3	1.700
Υ	0.425
Y1	0.800
Y2	1.150
Y3	1.450
Y4	2.300



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